Richard Keith Ahrenkiel
Natl. Renewable Energy Lab., Golden, CO, USA
For contributions to measurement of minority carrier lifetimes in semiconductor materials

Barry E. Burke
MIT Lincoln Laboratory, Lexington, MA, USA
For contributions to the technology development of charge-coupled devices for imaging and signal processing.

Sethumadhavan Chandrasekhar
Lucent Technologies, Holmdel, NJ, USA
For contributions to the design and development of 1.55 um opto-electronic integrated circuits for wide-spectrum application in optical communications.

Ih-Chin Chen
Worldwide Semiconductor Manufacturing, Hsin-Chu City, Taiwan
For leadership in the development of advanced CMOS technologies.

John D. Cressler
Auburn University, Auburn, AL, USA
For contributions to the understanding and optimization of silicon and silicon-germanium bipolar transistors.

Sorin Cristoloveanu
Natl. Center for Scientific Research, Grenoble, France
For contributions to Silicon-on-Insulator device physics, technology, and characterization.

Rik W.A.A. de Doncker
Aachen University of Technology, Aachen, Germany
For contributions to the development of high-power resonant soft-switching converters and high-performance digital control of induction machines.

Sang H. Dhong
IBM Austin Research Laboratory, Austin, TX, USA
For contribution to high speed processor and memory chip design.

Samir M. El-Ghazaly
Arizona State University, Tempe, AZ, USA
For contributions to the analysis and simulations of microwave devices and circuits.

Arthur Charles Gossard
Univ. of California, Santa Barbara, Santa Barbara, CA, USA
For contributions to semiconductor microstructure fabrication.
Aditya Kumar Gupta
Northrop Grumman Corporation, Linthicum, MD, USA
For contributions to the advancement of microwave monolithic integrated circuit technology and leadership in the development of manufacturable processes.

Yoshiaki Daimon Hagihara
Sony Corporation, Tokyo, Japan
For pioneering work on, and development of, solid-state imagers.

Takeo Hattori
Musashi Institute of Technology, Tokyo, Japan
For his contributions to the studies on the formation and the characterization of ultrathin gate oxides for ULSI devices.

James N. Hollenhorst
Agilent Laboratories, Palo Alto, CA, USA
For contributions to ultra-high performance avalanche photodiodes.

Wei Hwang
IBM T.J. Watson Research Center, Yorktown Heights, NY, USA
For contributions to high density cell technology and high speed Dynamic Random Access Memory design.

Hiroshi Ishiwara
Tokyo Institute of Technology, Yokohama, Japan
For contributions to Si-based heterostructure devices and ferroelectric memories.

Dieter Stefan Jager
Gerhard-Mercator-Universitat Duisburg, Duisburg, Germany
For contributions to the development of device concepts in microwaves and photonics.

Robert Forrest Kwasnick
General Electric Medical Systems, Santa Clara, CA, USA
For contributions to the development of amorphous silicon flat panel x-ray imager technology.

Kei May Lau
Hong Kong University of Science & Tech., Kowloon, Hong Kong
For contributions to III-V compound semiconductor heterostructure materials and devices.

Chin Chung Lee
University of California, Irvine, CA, USA
For pioneering research in fluxless bonding technology and contributions to thermal design tools for electronic devices and packages.

Baruch Levush
Naval Research Laboratory, Washington, DC, USA
For leadership in the development of theoretical and computational models of free electron radiation sources.
Bernard S. Meyerson
IBM T.J. Watson Research Center, Yorktown Heights, NY, USA
For the invention of ultra high vacuum chemical vapor deposition and its application
to low temperature epitaxy of SiGe for the fabrication of heterojunction bipolar
integrated circuits for telecommunications.

Akihiko Morino
NEC Corporation, Kanagawa, Japan
For contributions to the development of System-on-a-Chip for multimedia
applications.

Kenji Nishi
Semiconductor Leading Edge Technologies, Inc., Kanagawa, Japan
For contributions to semiconductor process and device modeling and the
development of software for their simulation.

Jon Harris Orloff
University of Maryland, College Park, MD, USA
For contributions to Focussed Ion Beam Technology.

Stephen John Pearton
University of Florida, Gainesville, FL, USA
For development of advanced semiconductor processing techniques and their
application to compound semiconductor devices.

John Xavier Przybysz
Northrop Grumman Corporation, Baltimore, MD, USA
For contributions in the development and application of Josephson digital circuits to
electronic systems, especially radars, communication satellites and data switching
networks.

Hans-Martin Rein
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For contributions to the design of high-speed silicon and silicon/germanium bipolar
circuits, especially as applied to fiber-optic systems.

Edward Anthony Rezek
TRW, Inc., Redondo Beach, CA, USA
For contributions to GaAs and InP monolithic microwave integrated circuits and
optoelectronic devices.

Arvind Kumar Sharma
TRW, Inc., Redondo Beach, CA, USA
For contributions to active device and passive component modeling, and design of
high power monolithic millimeter-wave integrated circuits.

Krishna Shenai
University of Illinois, Chicago, Chicago, IL, USA
For contributions to the understanding, development and application of power
semiconductor devices and circuits.
Ritu Shrivastava  
Alliance Semiconductor Corporation, Santa Clara, CA, USA  
For contributions to high performance CMOS memory technology and product development.

James C. Sturm  
Princeton University, Princeton, NJ, USA  
For contributions to novel silicon-based semiconductor devices, large-area electronics, and engineering education.

Peter Vettiger  
IBM Zurich Research Laboratory, Rueschlikon, Switzerland  
For contributions to and leadership in, the development of microfabrication processes for electronic, optoelectronic, and microelectromechanical devices, circuits, and systems.

Yang Yuan Wang  
Peking University, Beijing, China  
For leadership in China's semiconductor research and education

Isamu Washizuka  
Sharp Corporation, Nara, Japan  
For contributions to the technology and applications of liquid crystal displays.

Andrew B. Wittkower  
Soitec USA Inc., Peabody, MA, USA  
For contributions and leadership in the development and advancement of ion implantation techniques, equipment and companies.

Hon-Sum Phillip Wong  
IBM T.J. Watson Research Center, Yorktown Heights, NY, USA  
For contributions to solid-state image sensors and nanoscale CMOS devices.

Max Neil Yoder  
Office of Naval Research, Arlington, VA, USA  
For leadership of government sponsored development of microwave integrated circuits

The Nominations of the Following IEEE Members Were Evaluated by EDS But the individuals are Not Current Members of EDS

Karl W. Boer  
Solar Knoll, Kennett Square, PA, USA  
For contributions to research, development, and commercialization of thin film solar cells.

Satoshi Hiyamizu  
Osaka University, Osaka, Japan  
For contributions to the realization of the first high electron mobility transistor (HEMT).